

## **ABSTRACT**

The present technology relates to an electronic device and a method of manufacturing the same. The electronic device includes a semiconductor memory. The semiconductor memory includes  
5 row lines each extending in a first direction, column lines each extending in a second direction crossing the first direction, memory cells positioned at intersections of the row lines and the column lines, and including first sidewalls facing in the first direction and second sidewalls facing in the second direction, first  
10 protective layers respectively formed on the second sidewalls of the memory cells, and second protective layers respectively formed on the first sidewalls of the memory cells, and wherein a group of the second protective layers partially surround a sidewall of a corresponding one of the column lines.

15  
FIG. 2C